2018년 2월 7일(수), 13:15-14:45
Room F (봉래I, 6층)

F. Silicon and Group-IV Devices and Integration Technology 분과
[WF3-F] Photonics and Nanowire Technology

좌장: 김상완 교수(아주대학교), 안동환 교수(국민대학교)

WF3-F-1 **13:15-13:30**	**Ge-on-Insulator Structureusing Y_2O_3 for Mid-Infrared Photonics Platform** SangHyeon Kim[1,2,4], Jae-Hoon Han[1,4], Jae-Phil Shim[3], Hyung-Jun Kim[2,3], and Won Jun Choi[1] *[1]Center for Opto-Electronics Materials and Devices, KIST, [2]Nanomaterials Science and Engineering, UST, [3]Center for Spintronics, KIST*
WF3-F-2 **13:30-13:45**	**High Concentration Phosphorous Doping in Ge for CMOS-Integrated Laser Applications** Heedong Park[1], Motoki Yako[2], Yasuhiko Ishikawa[2], Kazumi Wada[2,3], and Donghwan Ahn[1] *[1]School of Materials Science and Engineering, Kookmin University, [2]Department of Materials Engineering, University of Tokyo, [3]Department of Materials Science and Engineering, MIT*
WF3-F-3 **13:45-14:00**	**Si Fin/$Si_{1-x}Ge_x$ Shell Channel p-Type FinFET for Sub-10-nm Technology Nodes and Its High-Speed Operation** Eunseon Yu[1], Won-Jun Lee[2], Jongwan Jung[2], and Seongjae Cho[1,3] *[1]Graduate School of IT Convergence Engineering, Gachon University, [2]Department of Nanotechnology and Advanced Materials Engineering, Sejong University, [3]Department of Electronics Engineering, Gachon University*
WF3-F-4 **14:00-14:15**	**Statistical Process-Induced Random Variation: Work-Function Variation in Stacked Nanowire FET** Jinyoung Park and Changhwan Shin *Department of Electrical and Computer Engineering, University of Seoul*
WF3-F-5 **14:15-14:30**	**A Characteristic of Stacked Gate-All-Around Nanowire MOSFET based on Source Drain Doping Profile** Suhyeon Kim, Junil Lee, Myung-Hyun Baek, Sihyun Kim, Ryoongbin Lee, Hyun-Min Kim, Kitae Lee, and Byung-Gook Park *Department of Electrical Engineering, Seoul National University*
WF3-F-6 **14:30-14:45**	**Simulation Study on the Effect of Unconformal Work-Function Metal Deposition on the Electrical Characteristic of Stacked-GAA MOSFET** Sihyun Kim[1], Suhyeon Kim[1], Sangwan Kim[2], Euyhwan Park[1], Junil Lee[1], Ryoongbin Lee[1], Soyeon Kim[1], Hyun-Min Kim[1], Kitae Lee[1], Jong-Ho Lee[1], and Byung-Gook[1] *[1]ISRC and Department of Electrical and Computer Engineering, Seoul National University, [2]Department of Electrical and Computer Engineering, Ajou University*